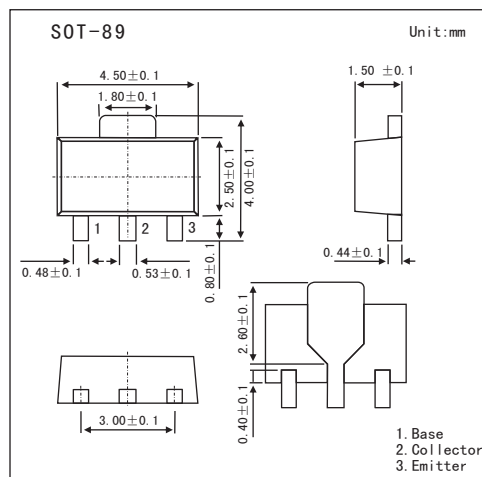


2SD1366A

■ Features

- Low frequency power amplifier



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	30	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	1	A
Total power dissipation	P _C *	1	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Value on the alumina ceramic board (12.5 × 20 × 0.7 mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = 10 μA, I _E = 0	30			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 1 mA, I _B = 0	25			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 10 μA, I _C = 0	5			V
Collector cutoff current	I _{CBO}	V _{CB} = 250V, I _B = 0			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 4 V, I _C = 0			0.1	μA
DC current gain	h _{FE}	V _{CE} = 2V, I _C = 500mA	85		240	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 0.8 A, I _B = 80mA			0.3	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C = 0.8 A, I _B = 80mA			1	V
Transition frequency	f _T	V _{CE} = 2V, I _C = 500mA		240		MHz
Output Capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz		22		pF

■ hFE Classification

Marking	AC	AD
hFE	82~180	120~240